ABSTRACT

INTEGRATED CIRCUIT SYSTEM INCLUDING NITRIDE LAYER TECHNOLOGY

An integrated circuit system including loading a wafer into a processing chamber and pre-purging the processing chamber with a first ammonia gas. Depositing a first nitride layer over the wafer and purging the processing chamber with a second ammonia gas. Depositing a second nitride layer over the first nitride layer that is misaligned with the first nitride layer. Post-purging the processing chamber with a third ammonia gas and purging the processing chamber with a nitrogen gas.

Fig. 18